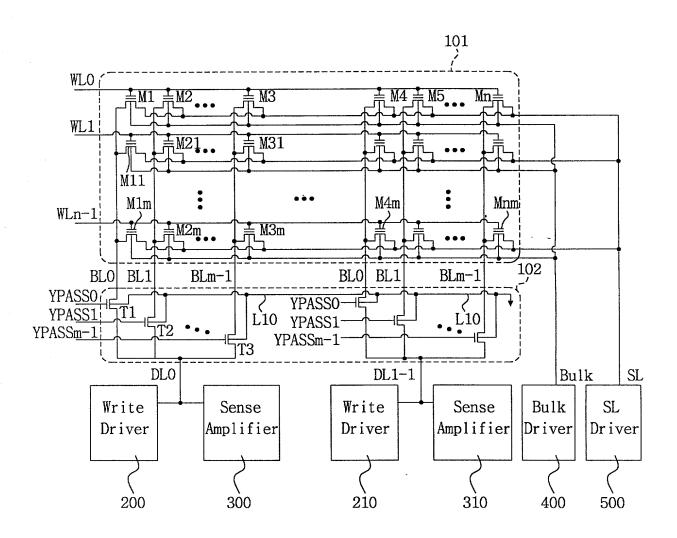
## FIG.1 (PRIOR ART)



## FIG.2 (PRIOR ART)

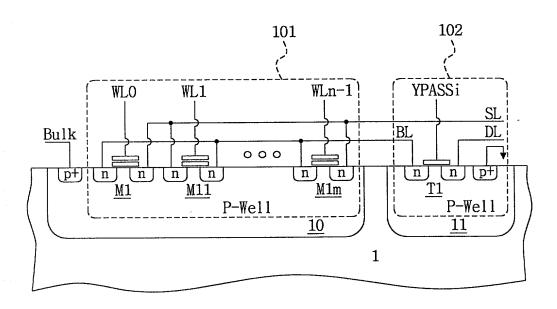


FIG.3

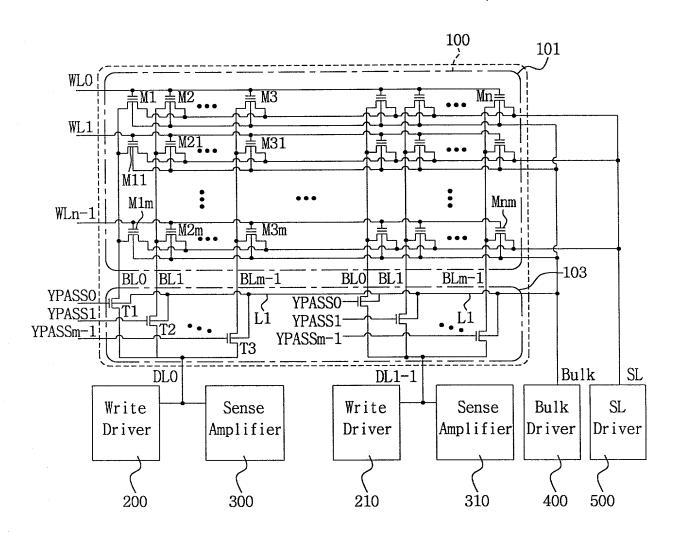


FIG.4

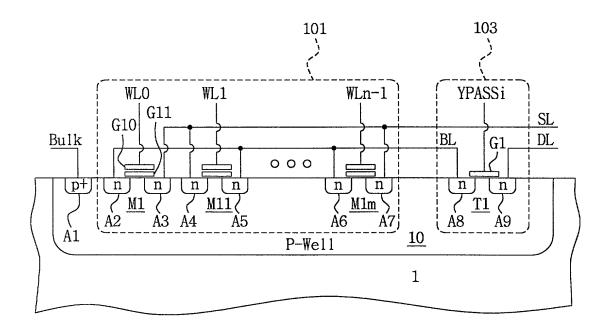


FIG.5

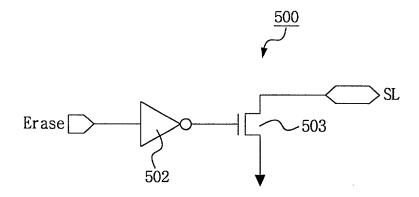


FIG.6

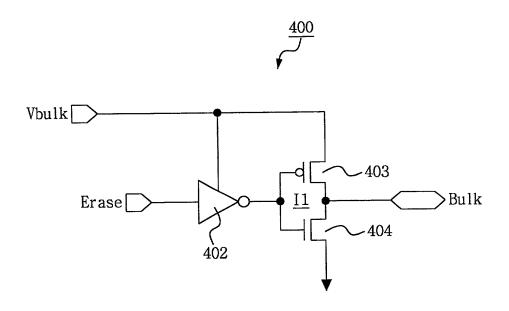
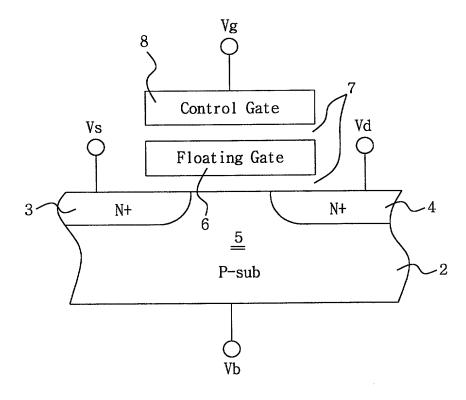


FIG.7 (PRIOR ART)



\* Byeong-Hoon LEE and Seung-Keun LEE

NONVOLATILE SEMICONDUCTOR MEMORY DEVICE .

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## FIG.8 (PRIOR ART)

Operation Mode	Vg	Vd	Vs	Vb
Program	+10V	+5V ~ +6V	OV	ov
Erase	-10V	Floating	Floating	+5V
Read	+4.5V	+1V	OV	ov